L Number		Search Text	_{DB}	Time stamp
1 Runber		((438/149) or (438/151) or (438/161) or	USPAT;	2003/08/15 13:32
	ļ	(438/164) or (438/166)).CCLS.	US-PGPUB;	1
1	i		EPO; JPO; DERWENT;	'
	!		IBM TDB	1
1 2	2960429	metal	USPĀT;	2003/08/15 13:32
İ			US-PGPUB;	
ļ			EPO; JPO; DERWENT;	
			IBM_TDB	
3	164C	(((438/149) or (438/151) or (438/161) or (438/161))	USPAT;	2003/08/15 13:33
İ	İ	(438/164) or (438/166)).CCLS.) and metal	US-PGPUB; EPO; JPO;	İ
			DERWENT;	!
	021212		IBM_TDB	0000/00/15 10 0.1
4	231313	protrusions	USPAT; US-PGPUB;	2003/08/15 13:34
į			EPO; JPO;	
	ļ		DERWENT;	
5	1 G	((((438/149) or (438/151) or (438/161) or	IBM_TDB USPAT;	2003/08/15 13:42
J	1,0	(438/164) or (438/166)).CCLS.) and metal)	US-PGPUB;	2003/06/13 13:42
	1	and protrusions	EPO; JPO;	
ı	!		DERWENT;	
! 6	1 2	(("6190949") or ("6096581")).PN.	IBM_TDB USPAT;	2003/08/15 13:42
		I	JS-PGPUB	2000/00/10 10:42
-	0	(the see of the see o	USPAT;	2002/08/14 11:43
		((non-single or poly or polycrystalline) adj (film or layer)) with recrystalliz\$4	JS-PGPUB; (EPO; JPO;	
i	1	i day (111m of 1afor), when reorgicalized	DERWENT;	İ
		0	IBM_TDB	
-	2	(heat adj absorb\$3) and insulat\$3 and (non-single or poly or polycrystalline)	USPAT; US-PGPUB;	2002/08/14 11:47
		adj (film or layer)) and recrystalliz\$4	EPO; JPO;	
	İ		DERWENT;	
i _	! ! 6766	(heat adj abscrb\$3) and insulat\$3	IBM_TDB USPAT;	2002/08/14 12:01
İ	1 0,00	(near day abbolbys) and insulates	US-PGPUB;	2002/06/14 12:01
			EPO; JPO;	
		i	DERWENT; IBM TOB	i i
_	2	! ((heat adj absorb\$3) and insulat\$3) and	USPAT;	2002/08/14 11:48
İ	i	((non-single or poly or polycrystalline)	US-PGPUB;	
i	•	adj (film or layer)) and recrystalliz\$4	EPO; JPO;	
1			DERWENT; IBM TDB	
-	0	((heat adj absorb\$3) with metal) and	, USPĀT;	2002/08/14 12:04
1	! :	insulat\$3 and amorphous and ((non-single	US-PGPUB;	į
		or poly or polycrystalline) adj (film or layer)) and recrystalliz\$4	EPO; JPO; DERWENT;	•
!		- I	IBM_TDB	1
-	0	((heat adj absorb\$3) with metal) and	USPĀT;	2002/08/14 12:05
		insulat\$3 and ({ amorphous or non-single or poly or polycrystalline) adj (film or	US-PGPUB; EPO; JPO;	ļ
1	' 	layer)) and recrystalliz\$4	DERWENT;	İ
j _	1320	(heat add absorbed) with matal	IBM_TDB	2000/00/11 12 15
i	1320	(heat adj absorb\$3) with metal	USPAT; US-PGPUB;	2002/08/14 12:15
	į		EPO; JPO;	
1			DERWENT;	
-	499	((heat adj absorb\$3) with metal) and	IBM_TDB USPAT;	2002/08/14 12:06
!	i	insulat\$3	JS-PGPUB;	1
			EPO; JPO;	i İ
i	i '		DERWENT; IBM TDB	\ ;
	· — — ·			

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	₄ .	(((heat ad; absorb\$3) with metal) and	USPAT;	2002/08/14 12:08
	:	insulat\$3) and (non-single or poly or	US-PGPUB;	i İ
		polycrystalline) and recrystalliz\$4	EPO; JPO;	
i	1		DERWENT;	`
			! IBM_TDB	2002/02/14 12:20
-	24	(((heat adj absorb\$3) with metal) and	USPAT;	2002/08/14 12:08
i		insulat\$3) and (non-single or poly or	US-PGPUB;	i
,		polycrystalline)	EPO; JPO;	j
		1	DERWENT;	i
_	1000052	((heat adj absorb\$3 or metal) adj layer or	USPAT;	2002/08/14 18:08
1	1 1500052	film)	US-PGPUB;	2002/00/11 10:03
!			EPO; JPO;	
	•		DERWENT;	
			IBM TDB	İ
_	13	(heat adj absorb\$3 with metal) adj (layer	USPAT;	2002/08/14 12:19
	İ	or film)	US-PGPUB;	!
i	ļ		EPO; JPO;	
			DERWENT;	
į	•		IBM_TDB	
-	538	(heat adj absorb\$3) adj (layer or film)	USPAT;	2002/08/14 12:39
•			US-PGPUB;	1
			EPO; JPO;	1 :
	1	· ·	DERWENT;	
i _	1	///host add absorbs3) add (layor or film))	IBM_TDB USPAT;	2002/08/14 12:21
-	ļ	<pre>(((heat adj absorb\$3) adj (layer or film)) same metal) and polycrystalline</pre>	US-PGPUB;	2002/06/14 12:21
		:	EPO; JPO;	
			DERWENT;	1
		İ	IBM TDB	
-	I C	(((heat adj absorb\$3) adj (layer or film))	USPAT;	2002/08/14 12:21
	!	same metal) and recrystalliz\$4	US-PGPUB;	
	1	•	EPO; JPO;	ļ
	·		DERWENT:	
<u> </u>		i	IBM_TDB	i
-	105	((heat adj absorb\$3) adj (layer or film))	USPAT;	2002/08/14 12:22
	1	same metal	US-PGPUB;	1
	ļ		EPO; JPO;	· .
	1		DERWENT;	!
i _	1	((heat adj absorb\$3) adj (layer or film))	'IBM_TDB USPAT;	2002/08/14 12:39
! -		with tft	US-PGPUB;	
		with tit	EPO; JPO;	
	i		DERWENT;	1
i	ļ		IBM TDB	· · · · · · · · · · · · · · · · · · ·
-	20154	((heat adj absorb\$3 or metal) adj layer or	USPAT;	2002/08/14 15:18
		film) and tft	US-PGPUB;	
:			EPO; JPO;	
		· !	DERWENT;	1
	1		IBM_TOB	
-	3477	(((heat adj absorb\$3 or metal) adj layer	USPAT;	2002/08/14 15:19
	1	or film) and tft) and polycrystalline	US-PGPUB;	i
1			EPO; JPO; DERWENT;	1
		1	IBM TDB	1
_	1 2873	((((heat adj absorb\$3 or metal) adj layer	USPAT;	2002/08/14 15:20
İ		or film) and tft) and polycrystalline) and	US-PGPUB;	
1		insulat\$3	EPO; JPO;	ľ
			DERWENT;	
ı		İ	IBM_TDB	1
_	0	(((((heat adj absorb\$3 or metal) adj layer	USPĀT;	2002/08/14 15:21
i	ļ	or film) and tft) and polycrystalline) and	US-PGPUB;	'
ļ	İ	insulat\$3) and irradat\$3	EPO; JPO;	
			DERWENT;	•
	1000	(////	IBM_TDB	1 2002 /02 /1 4 4 5 22
_	1208	, , , , , ,	USPAT;	2002/08/14 15:22
	Ì	or film) and tft) and polycrystalline) and insulats 31 and crystallizes	US-PGPUB;	1
	i	insulat\$3) and crystalliz\$5	EPO; JPO; DERWENT;	į
1			IBM TDB	i
<u> </u>	·			

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		_		
	628	((((((neat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and crystalliz\$5) and island\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002708/14 15: <u>22</u> i
-	615	(((((((heat adj absorb\$3 or metal) adj layer or film) and tft) and	<pre>IBM_TDB USPAT; US-PGPUB;</pre>	j 20C2/08/14 15:23
-	35	polycrystalline) and insulat\$3) and crystalliz\$5) and island\$1) and semiconductor ((((((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/08/14 18:12
-	o	crystalliz\$5) and island\$1) and semiconductor) and protrusion\$1 irradat\$4 with protrusion\$1	DERWENT; IBM_TDB USPAT;	2002/08/14 17:14
<u> </u>	ļ 		US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	; !
-	400	irradiat\$4 with protrusion\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/14 17:23
	j 1	! (irradiat\$4 with protrusion\$1) with tft	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/14 17:16
-	0	((irradiat\$4 with protrusion\$1) with tft) with crystalliz\$5	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/08/14 17:17
 -	9	((irradiat\$4 with protrusion\$1) with tft) and crystalliz\$5	DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/08/14 17:17
-	j 24	<pre>irradiat\$4 with (protrusion\$1 same semiconductor)</pre>	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/08/14 17:23
_	220	irradiat\$4 and (protrusion\$1 same	EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/08/14 17:24
į		semiconductor)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB]
	0	<pre>metal with insulat\$3 with amorphous with irradat\$4</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/14 18:06
_	21	<pre>metal and insulat\$3 and amorphous and irradat\$4</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/08/14 18:07
- 	121266	metal adj(layer or film)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/08/14 18:08
-	121266	 metal adj (layer or film)	DERWENT; IBM_TDB USPAT; US-PGPUB;	i ^{2002/08/14} 18:09
<u> </u>			EPO; JPO; DERWENT; IBM_TDB	<u> </u>

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			_			
	i	3067	(metal adj (layer or film)) and tft	Tuspat; US-PGPUB;	202/08/14 18:09	.,
j j	İ			EPO; JPO; DERWENT; IBM TDB	ļ	
· -			((metal adj (layer or film)) and tft) and insulat\$4	USPĀT; US-PGPUB;	2002/08/14 18:09	
<u> </u>				EPO; JPO; DERWENT; IBM TDB		
-		613	(((metal adj (layer or film)) and tft) and insulat\$4) and crystalliz\$5	USPAT; US-PGPUB; EPO; JPO;	2002/08/14 18:11	i
j			!	DERWENT; IBM_TDB		ļ
-		368	((((metal adj (layer or film)) and tft) and insulat\$4) and crystalliz\$5) and irradiat\$4	USPAT; US-PGPUB; EPO; JPO;	2002/08/14 18:13	
i -	<u> </u>	53	 (((((metal adj (layer or film)) and tft)	DERWENT; IBM_TDB USPAT;	2002/08/14 18:13	ļ ļ
	ļ		and insulat\$4) and crystalliz\$5) and irradiat\$4) and (semiconductor adj island)	US-PGPUB; EPO; JPO; DERWENT;		
	1		İ	IBM_TDB	1]
-	!	53	<pre>(((((((metal adj (layer or film)) and tft) and insulat\$4) and crystalliz\$5) and irradiat\$4) and (semiconductor adj</pre>	USPAT; US-PGPUB; EPO; JPO;	2002/08/14 18:14	1
, -	1	С	island)) and electrode tft with island\$1 with amorphous with	DERWENT; IBM_TDB USPAT;	2002/08/15 10:35	l İ
!	ļ		crystalliz\$5 with irradat\$4 !	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	 	ı
-		0	tft and island\$1 with amorphous near5 crystalliz\$5 with irradat\$4	USPAT; US-PGPUB; EPO; JPO;	2002/08/15 10:35	
•				DERWENT; IBM TDB		
-		О	tft and island\$1 and amorphous near5 crystalliz\$5 with irradat\$4	USPĀT; US-PGPUB; EPO; JPO;	2002/08/15 10:36]
ļ				DERWENT; IBM_TDB	ļ	
j	 - 	1	tft with island\$1 with amorphous near5 crystalliz\$5 with irradiat\$4	USPĀT; US-PGPUB; EPO; JPO;	1 2002/08/15 10:36	
Ĺ				DERWENT; IBM TDB	 	
-	İ		20010045558.URPN. 2001C045558.URPN.	USPĀT USPĀT	2002/08/15 15:29 2002/08/15 15:29	
-	ļ		protrusion\$1 with crystalliz\$5 adj semiconductor	USPAT; US-PGPUB;	2002/08/15 19:08	l
	l	ļ		EPO; JPO; DERWENT; IBM TDB	l	1
-	!	1	(rough\$4 with recrystalliz\$5) with hsg	USPAT; US-PGPUB; EPO; JPO;	2002/08/15 19:09	İ
	I			DERWENT; IBM TDB	İ	I
-	i		20020036312.URPN. rough\$4 same recrystalliz\$5	USPAT USPAT; US-PGPUB;	2002/08/15 19:10 2002/08/15 19:12	į
į	<u> </u> 	ļ		EPO; JPO; DERWENT; IBM TDB	İ	i
	'			. = = = = =		

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			•••	
[=	 292	rough\$4 with recrystalliz\$5	USPAT; US-PGPUB;	2002/08/15 19:46
	ļ		EPO; JPO; DERWENT; IBM TDB	-
-	8	(rough\$4 with recrystalliz\$5) with amorphous	USPĀT; US-PGPUB;	i 2002/08/15 19:14
·	i	\ 	EPO; JPO; DERWENT; IBM_TDB	
- 		20020034845.URPN. ("4411734" "4737474" "5089432" "5121186" "5147820" "5147826"	USPAT USPAT	2002/08/15 19:18 2002/08/15 19:23
	I	"5298436" "5326722" "5418398" "5441904" "5514621" "5604157" "5614428" "5652156" "5712181").PN.	!	i i
_	. 2	6017819.URPN.	USPAT	2002/08/15 19:39
í -	0	20020036312.URPN.	USPAT	2002/08/15 19:45
`-	. 5	(rough\$4 with recrystalliz\$5) with semiconductor	USPAT; US-PGPUB; EPO; JPO;	2002/08/15 19:47
ļ		:	DERWENT; IBM_TDB	0000 (00 (15, 10, 01
i -		((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.	USPAT; US-PGPUB	2003/08/15 13:31
-	99764	irradiate or irradiation	USPAT; US-PGPUB	12003/04/06 17:45
-	595	(((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)	USPAT; US-PGPUB	2003/04/06 17:46
-	1217179	metal	USPAT; US-PGPUB	2003/04/06 17:46
i I	497 	((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal	! USPAT; US-PGPUB	2003/04/06 17:46
' -		channel	USPAT; US-PGPUB	2003/04/06 17:46
	Ì	(((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal) and channel	USPAT;	2003/04/06 17:48
-	ļ	semiconductor	USPAT; US-PGPUB	2003/04/06 17:48
-	1	((((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal) and channel) and semiconductor	USPAT; US-PGPUB	2003/04/06 17:48
į –	661709 i		USPAT;	2003/04/06 17:50
-	141	(((((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal) and	USPAT; US-PGPUB	2003/04/06 1 7:50
ì		channel) and semiconductor) and	1	
¦ -		(protrusion or project or projection) ("5581092" "5959313" "6281057" ["6323071").PN.	USPAT	2003/04/06 19:12
-	0	6506669.URPN.	USPAT	2003/04/06 19:13
i	 C_	6506669.URPN.	USPAT	2003/04/06 19:13